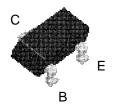


**July 1998** 

# **FSB560 / FSB560A**



SuperSOT<sup>™</sup>-3 (SOT-23)

### **NPN Low Saturation Transistor**

These devices are designed with high current gain and low saturation voltage with collector currents up to 2A continuous.

Absolute Maximum Ratings\* T<sub>A = 25°C unless otherwise noted</sub>

Symbol	Parameter	FSB560/FSB560A	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V
V <sub>CBO</sub>	Collector-Base Voltage	80	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
Ic	Collector Current - Continuous	2	А
T <sub>J,</sub> T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150  $^{\circ}\text{C}.$
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Thermal Characteristics T<sub>A = 25°C unless otherwise noted</sub>

Symbol	Characteristic	Max	Units
		FSB560/FSB560A	
P <sub>D</sub>	Total Device Dissipation	500	mW
R <sub>θ</sub> JA	Thermal Resistance, Junction to Ambient	250	°C/W

NPN	Low	Saturation	<b>Transistor</b>

(continued)

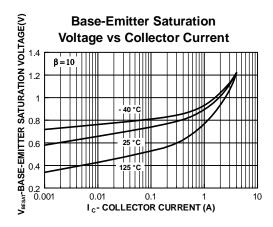
ヘナドルヘコ	I ( hars	OCHOPICHICS
cu ica	ı Gilaic	acteristics

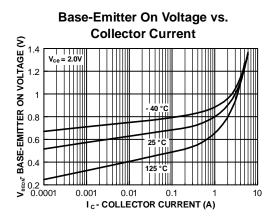
 $T_{\text{A}\,=\,25^{\circ}\text{C}\,\text{unless otherwise noted}}$ 

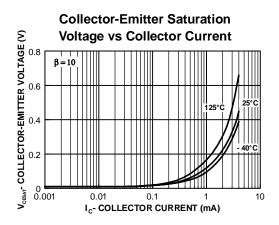
Symbol	Parameter	Test Conditions	Min	Max	Units	
OFF CHAI	RACTERISTICS					
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10 mA	60		V	
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 100 μA	80		V	
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 100 μA	5		V	
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 30 V		100	nA	
		V <sub>CB</sub> = 30 V, T <sub>A</sub> =100°C		10	uA	
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V		100	nA	
ON CHAR	ACTERISTICS*			T	1	
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 100 mA, V <sub>CE</sub> = 2 V	70		-	
		I <sub>C</sub> =500mA, V <sub>CE</sub> =2V <b>FSB560</b>	100	300		
		FSB560A	250	550		
		I <sub>C</sub> = 1 A, V <sub>CE</sub> = 2 V	80			
		I <sub>C</sub> = 2 A, V <sub>CE</sub> = 2 V	40			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1 A, I <sub>B</sub> = 100 mA		300	m۷	
-()		I <sub>C</sub> = 2 A, I <sub>B</sub> =200 mA <b>FSB560</b>		350		
		FSB560A		300		
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1 A, I <sub>B</sub> = 100 mA		1.25	V	
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 1 A, V <sub>CE</sub> = 2 V		1	V	
SMALL SI	GNAL CHARACTERISTICS					
C <sub>obo</sub>	Output Capacitance	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1MHz		30	pF	
f⊤	Transition Frequency	I <sub>C</sub> = 100 mA,V <sub>CE</sub> = 5 V, f=100MHz	75		-	

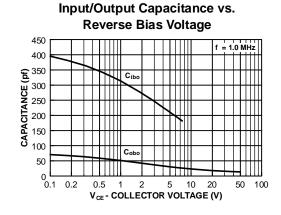
\*Pulse Test: Pulse Width  $\leq 300~\mu s,~Duty~Cycle \leq 2.0\%$ 

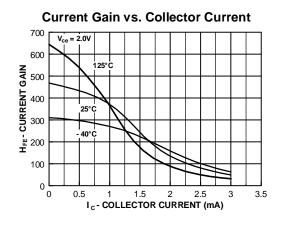
# **Typical Characteristics**

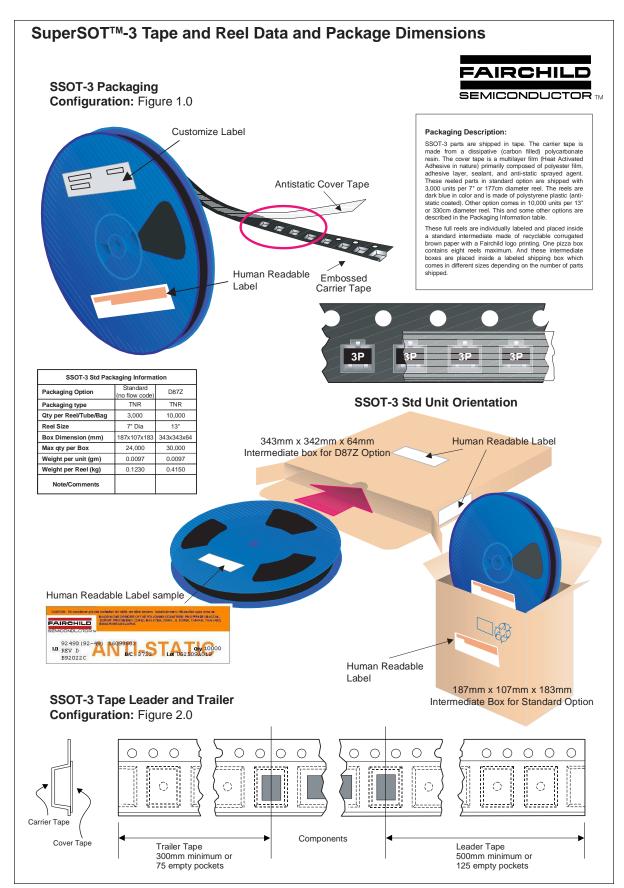








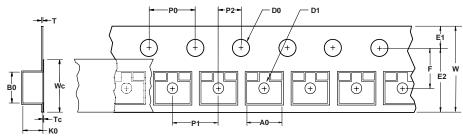


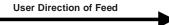




# SSOT-3 Embossed Carrier Tape

Configuration: Figure 3.0



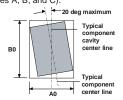


	Dimensions are in millimeter													
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-3 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-02

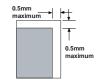
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

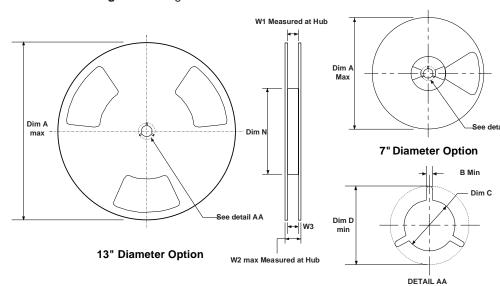


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

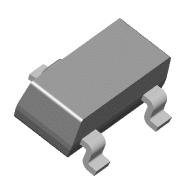
### SSOT-3 Reel Configuration: Figure 4.0

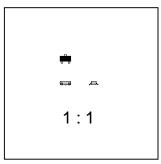


	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

# SuperSOT™-3 Tape and Reel Data and Package Dimensions, continued

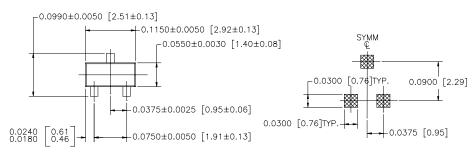
# SuperSOT™-3 (FS PKG Code 32)



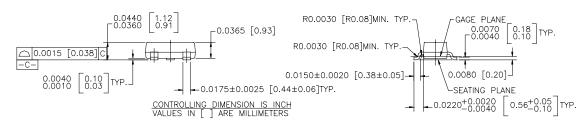


Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0097



LAND PATTERN RECOMMENDATION



NOTES: UNLESS OTHERWISE SPECIFIED

SUPER SOT , 3 LEADS

- 1. STANDARD LEAD FINISH TO BE 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER.
- 2. NO JEDEC REGISTRATION AS OF DEC. 1995.

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E<sup>2</sup>CMOS<sup>™</sup> PowerTrench<sup>™</sup>

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 $\begin{array}{lll} \mathsf{FACT} \ \mathsf{Quiet} \ \mathsf{Series^{\mathsf{TM}}} & \mathsf{Quiet} \ \mathsf{Series^{\mathsf{TM}}} \\ \mathsf{FAST}^{\otimes} & \mathsf{SuperSOT^{\mathsf{TM}}}\text{-}3 \\ \mathsf{FASTr^{\mathsf{TM}}} & \mathsf{SuperSOT^{\mathsf{TM}}}\text{-}6 \\ \mathsf{GTO^{\mathsf{TM}}} & \mathsf{SuperSOT^{\mathsf{TM}}}\text{-}8 \\ \mathsf{HiSeC^{\mathsf{TM}}} & \mathsf{TinyLogic^{\mathsf{TM}}} \\ \end{array}$ 

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- A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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